SCHOTTKY DIODES

Silicon Schottky Barrier Diodes in DO-35 Package
for general purpose applications with low forward voltage drop and very fast switching times.
Using the type designations **LL101A, LL103A,** and so on, these Schottky Barrier diodes are available in the MiniMELF package with the same electrical characteristics.

Type	Peak Inv. Voltage PIV	Power Dissipation at 25 °C	Junction and Storage Temp.	Forward Voltage Drop V_F at I_F				Reverse Current I_R at V_R		Capacitance at $V_F = V_R = 0$, f = 1 MHz	Reverse Recovery Time t_{rr}	
	Volts	max. mW	max. °C	max. V	at mA	max. V	at mA	max. µA	at V	max. pF	max. ns	Conditions
SD101A*	60	400	200	0.41	1	1.0	15	0.2	50	2.0	1	$I_F = I_R = 5$ mA to 0.1 I_R
SD101B	50	400	200	0.40	1	0.95	15	0.2	40	2.1	1	$I_F = I_R = 5$ mA to 0.1 I_R
SD101C	40	400	200	0.39	1	0.90	15	0.2	30	2.2	1	$I_F = I_R = 5$ mA to 0.1 I_R
SD103A	40	400	125	0.37	20	0.6	200	5.0	30	50	10	$I_F = I_R = 200$ mA to 0.1 I_R
SD103B	30	400	125	0.37	20	0.6	200	5.0	20	50	10	$I_F = I_R = 200$ mA to 0.1 I_R
SD103C	20	400	125	0.37	20	0.6	200	5.0	10	50	10	$I_F = I_R = 200$ mA to 0.1 I_R

* JEDEC Equivalent: 1N6263

SOLID STATE TUNER COMPONENTS

Variable-Capacitance Tuner Diodes (delivered in matched sets)

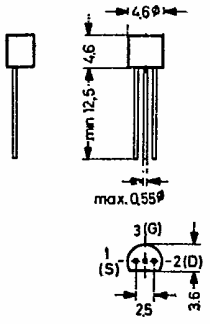
Type	Package	Capacitance			Capacitance Ratio				Series Resistance				Reverse Current	
		min. pF	max. pF	at V_R V	min.	max.	at V_R = V	to V	Ω typ.	Ω max.	at f MHz	and C pF	max. nA	at V_R V
BB221	DO-35	1.8	2.2	28	8.0	9.5	1	28	0.55	0.7	470	9	30	30
BB222	DO-35	1.8	2.5	28	7.3	9.5	1	28	0.80	1.0	470	9	30	30
BB329	DO-35	2.5	3.2	28	12	–	1	28	0.85	–	330	25	30	30
BB404A* **	TO-236	42	43.5	2	1.65	1.75	2	8	–	0.4	100	38	20	10
BB404B	TO-236	43	44.5	2	1.65	1.75	2	8	–	0.4	100	38	20	10
BB404C	TO-236	44	45.5	2	1.65	1.75	2	8	–	0.4	100	38	20	10
BB404D	TO-236	45	46.5	2	1.65	1.75	2	8	–	0.4	100	38	20	10
BB404E	TO-236	46	47.5	2	1.65	1.75	2	8	–	0.4	100	38	20	10
BB510	TO-236**	440	600	1	15	–	1	9	–	–	–	–	30	10
BB521*	DO-35	1.8	2.2	28	8.0	9.5	1	28	0.55	0.7	470	9	30	30
BB523	DO-35	1.9	2.25	28	9.5	15	1	28	–	0.8	470	14	30	30
BB529*	DO-35	2.5	3.2	28	12	–	1	28	0.85	–	330	25	30	30
BB531	DO-35	3.15	3.55	28	19.5	25	1	28	0.9	1.0	300	25	30	30
BB601	≈60A2	0.9	1.2	28	8.0	9	1	28	–	1.2	470	9	30	30
BB621*	MiniMELF	1.8	2.2	28	8.0	9.5	1	28	0.55	0.7	470	9	30	30
BB622	MiniMELF	1.8	2.5	28	7.3	9.5	1	28	0.80	1.0	470	9	30	30
BB623	MiniMELF	1.9	2.25	28	9.5	15	1	28	–	0.8	470	14	30	30
BB629*	MiniMELF	2.5	3.2	28	12	–	1	28	0.85	–	330	25	30	30
BB631	MiniMELF	3.15	3.55	28	19.5	25	1	28	0.9	1.0	300	25	30	30
BB721	≈60A2	2.0	2.29	28	8.0	–	1	28	–	0.5	470	14	30	30
BB723	≈60A2	1.9	2.25	28	9.5	15	1	28	–	0.8	470	14	30	30
BB729	≈60A2	2.38	2.93	28	12	–	1	28	–	0.8	470	25	30	30
BB730	≈60A2	2.7	2.9	28	14.8	16.8	1	28	–	0.9	330	25	30	28
BB731	≈60A2	3.15	3.55	28	19.5	25	1	28	0.9	1.0	300	25	30	30

* These types are successors of types BB221 and BB329 respectively, providing an improved linearity of the capacitance versus reverse bias curve.
** Pins 1 and 2: Cathode, Pin 3: Anode
*** The types BB404 are dual capacitance diodes with common cathode. Pin 1: Cathode, Pin 2: Anode 1, Pin 3: Anode 2.

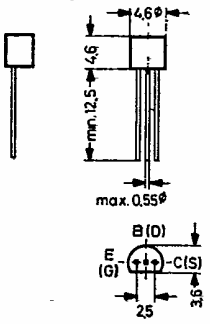
PACKAGE OUTLINES

All Dimensions in mm

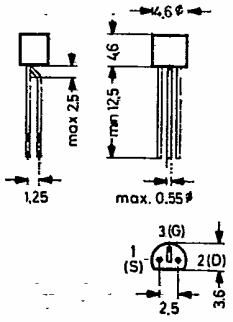
TO-92 Plastic Package (10D3)
Pin in-Line "A"
Weight approx. 0.18 g



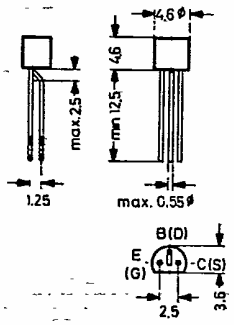
TO-92 Plastic Package (10D3)
Pins in-Line "B"
Weight approx. 0.18 g



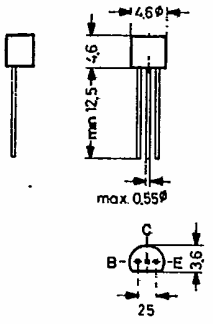
TO-92 Plastic Package
Pins TO-18 "A"
Weight approx. 0.18 g



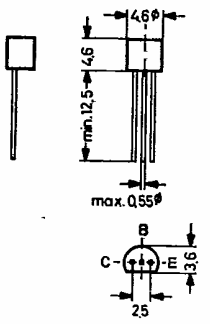
TO-92 Plastic Package
Pins TO-18 "B"
Weight approx. 0.18 g



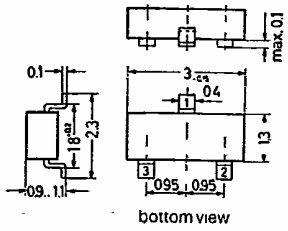
TO-92 Plastic Package
Pins in-Line "D"
Weight approx. 0.18 g



TO-92 Plastic Package
Pins in-Line "E"
Weight approx. 0.18 g



TO-236 Plastic Package (23A3)
Weight approx. 0.01 g



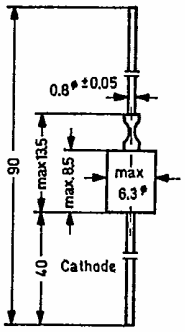
bottom view

ITT Components

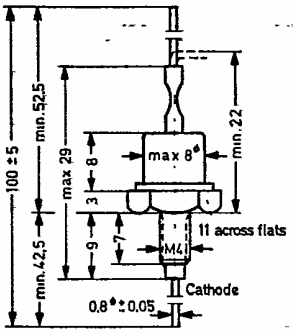
PACKAGE OUTLINES

All Dimensions in mm

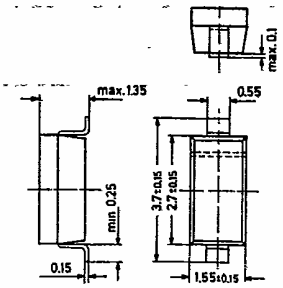
DO-13 Metal Case
Weight approx. 1.4 g



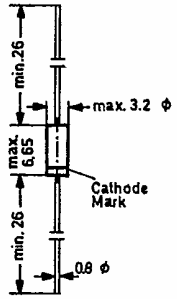
Stud-Mounted Metal Case
Weight approx. 6 g



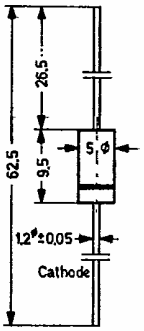
≈60A2 Diode Plastic Package
Weight approx. 0.013 g



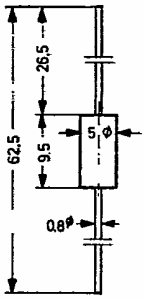
Diode Plastic Package P1
Weight approx. 0.4 g



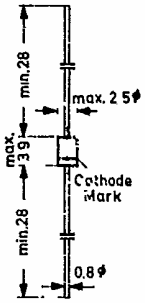
Diode Plastic Package P2
Weight approx. 1 g



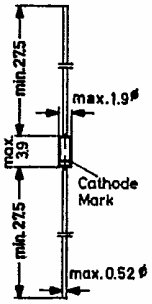
Diode Plastic Package P3
Weight approx. 0.6 g



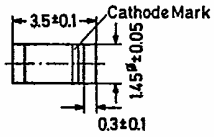
DO-41 Glass Case
Weight approx. 0.35 g



DO-35 Glass Case
Weight approx. 0.13 g



MiniMELF Glass Case
Weight approx. 0.05 g



MELF Glass Case
Weight approx. 0.25 g